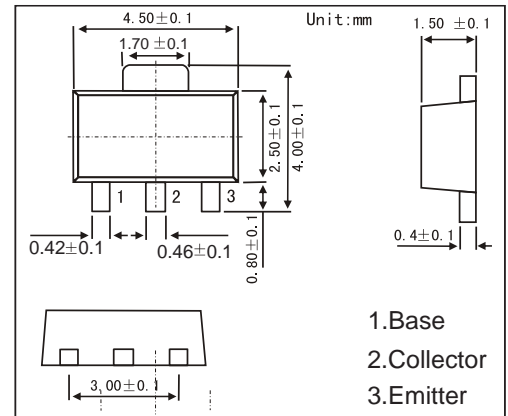


**SOT-89 Plastic-Encapsulate Transistors**
**FEATURES**

- Subminiature encapsulated flat polarized relay

**MECHANICAL DATA**

- Case style:SOT-89molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-0.4	A
Collector Power Dissipation	$P_C$	0.5	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -80V, I_E = 0$			-0.1	μA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -50mA$	70		240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -200mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200mA, I_B = -20mA$			-0.4	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -2V, I_C = -5mA$	-0.55		-0.8	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -10mA$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		14		pF